## In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims**

## 1. - 25. (Canceled)

26. (New): A programmable resistor device in an integrated circuit device, comprising:

a substrate with individual lines disposed between a first terminal and a second terminal, wherein any of the individual lines may be blown open by a current forced from the first terminal to the second terminal; and

a first line of the individual lines having a resistance different from a second line.

- 27. (New): The device according to claim 26 wherein the resistance of the first line is lower than that of the second line.
- 28. (New): The device according to claim 26 wherein a line width of the second line is wider than that of the first line.
- 29. (New): The device according to claim 26 wherein the substrate comprises a semiconductor layer.
- 30. (New): The device according to claim 29 wherein the semiconductor layer comprises silicon or polysilicon.

- 31. (New): The device according to claim 26 wherein the programmable resistor device is a chip identifier for the integrated circuit device.
- 32. (New): The device according to claim 26, wherein the individual lines comprise a semiconductor layer.
  - 33. (New): A programmable resistor device in an integrated circuit device, comprising:

a substrate with individual lines disposed between a first terminal and a second terminal, wherein any of the individual lines may be blown open by a current forced from the first terminal to the second terminal; and

a layer of metal or metal-semiconductor alloy overlying a first line of the individual lines but not a second line of the individual lines, the first line with the layer of metal or metal-semiconductor alloy having a resistance smaller than that of the second line.

- 34. (New): The device according to claim 33, wherein the metal comprises metal silicide.
- 35. (New): The device according to claim 33 wherein the substrate comprises semiconductor layer.
- 36. (New): The device according to claim 33 wherein the semiconductor layer comprises silicon or polysilicon.
  - 37. (New): The device according to claim 33, wherein the lines comprise a semiconductor layer.

38. (New): A programmable resistor device in an integrated circuit device, comprising:

a substrate with individual lines disposed between a first terminal and a second terminal, wherein any of the individual lines may be blown open by a current forced from the first terminal to the second terminal; and

a first line of the individual lines with a first dopant concentration and a second line of the individual lines with a second dopant concentration, the first line having a resistance smaller than that of the second line.

- 39. (New): The device according to claim 38 wherein the substrate comprises semiconductor layer.
- 40. (New): The device according to claim 38 wherein the semiconductor layer comprises silicon or polysilicon.